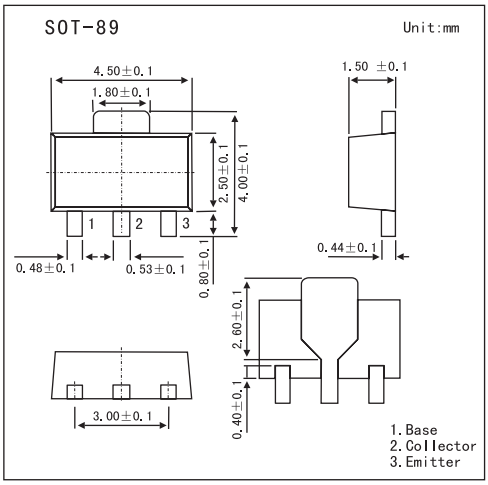
Low Frequency Transistor

2SB1386



■ Features

- Low VCE(sat).
  VCE(sat) = -0.35V (Typ.)
  (IC/IB = -4A / -0.1A)
- Excellent DC current gain
- Epitaxial planar type
- PNP silicon transistor

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-5	A
Collector current(Pulse)	I_{CP} *	-10	A
Collector power dissipation	P_C	0.5	W
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-55 to +150	℃

* Single pulse, Pw=10ms

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=-50μA	-30			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=-1mA	-20			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-50μA	-6			V
Collector cutoff current	I_{CBO}	V_{CB}=-20V			-0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB}=-5V			-0.5	μA
DC current transfer ratio	$V_{CE(sat)}$	I_C=-4A,I_B=-0.1A			-1	V
Collector-emitter saturation voltage	hFE	V_{CE}=-2V, I_C=-0.5A	82		390	
Transition frequency	Cob	V_{CE}=-6V, I_E=50mA, f=30MHz		120		MHz
Output capacitance	fT	V_{CB}=-20V, I_E=0A, f=1MHz		60		pF

■ hFE Classification

Marking	BH		
Rank	P	Q	R
hFE	82～180	120～270	180～390